Diode Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-092-9502

lu al casa at	
Inclosure N	aterial:
Metal	
Overall Len	-
0.450 inches	
-	acility Quantity:
1 Joint Electr	onic Device Engineering Council/jedec/case Outline Designation:
Do-5	onic Device Engineering Council/jedec/case Outline Designation:
	nternally-electrically Connected To Case:
Anode	iternally-electrically connected to case.
Mounting N	lethod.
Threaded st	
Features Pr	
	sealed case
-	th Across Flats:
0.687 inches	
Thread Size	
0.250 inches	
	, ctor Material:
Silicon	
	ing In Volts Per Characteristic:
8.6 regulate	-
-	ing Per Characteristic:
	es repetitive peak forward current
-	ng Per Characteristic:
	mall-signal input power, common-collector preset
	perating Tempurature Per Measurement Point:
	es celsius ambient air
Test Data D	
81349-mil-s-	19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specificatio
format; excl	udes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environment	al and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Seri	es Designator:
Unf	
Terminal Ty	rpe And Quantity:
1 tab, solde	r lug and 1 threaded stud
Specificatio	n Data:
81349-mil-s·	19500/358 government specification
Shelf Life:	
N/a	
Unit Of Mea	sure:
Demilitariza	ition:
No	

NSN 5961-01-092-9502

Diode Semiconductor Device - Page 2 of 2

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